

STROBE FLASHER USE

PERFORMANCE CURVES

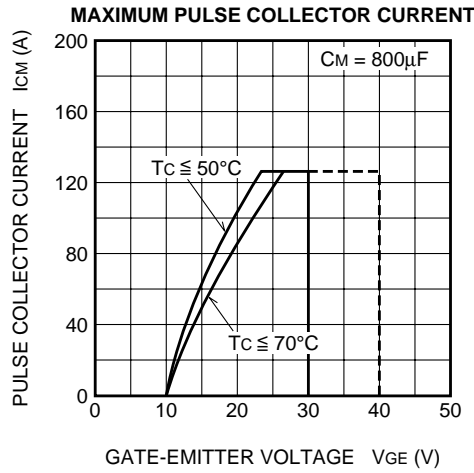


Figure 1

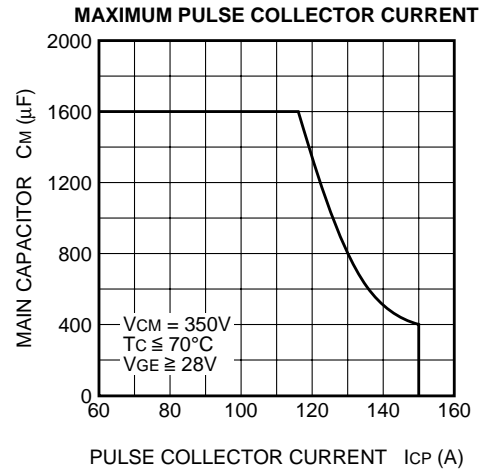
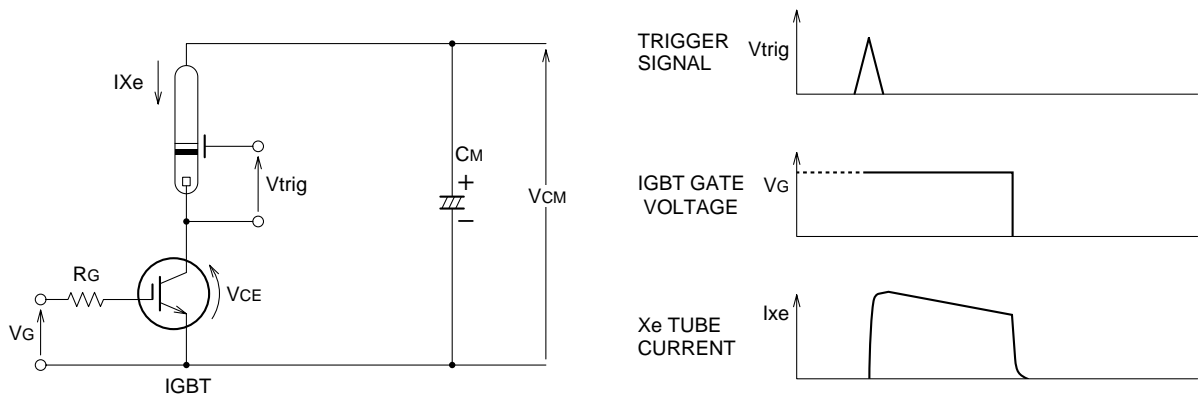


Figure 2

APPLICATION EXAMPLE



RECOMMEND CONDITION	MAXIMUM CONDITION
$V_{CM} = 330\text{V}$	360V
$I_P = 120\text{A}$	130A
$C_M = 700\mu\text{F}$	800 μF
$V_{GE} = 28\text{V}$	

- Notice 1. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current. And reverse gate current during turn-off must be kept less than 1A. (In general, it is satisfied if $R_G \geq 30\Omega$)
- Notice 2. IGBT has MOS structure and its gate is insulated by thin silicon oxide. So please handle carefully not to suffer from electrostatic charge.
- Notice 3. The operation life should be endured 5,000 shots under the charge current ($I_{xe} \leq 130\text{A}$: full luminescence condition) of main condenser ($C_M=800\mu\text{F}$). Repetition period under full luminescence condition is over 3 seconds.
- Notice 4. Total operation hours must be applied within 5,000 hours.